

ABSTRACT OF THE DISCLOSURE

Although there is provided a high light transmittance of an emitted light by a ITO electrode film conventionally employed, there occurs a formation of a Schottky type contact between the ITO electrode film and a p type GaN system semiconductor layer, thus resulting in a not uniform flow of an electric current. It is an object of the present invention to provide a semiconductor light emitting device constituted by forming a transparent electrode, which facilitates acquiring an ohmic property, to be replaced by an ITO electrode film, at the light extracting or light exit side of the GaN system semiconductor light emitting device, so as to improve a light emission efficiency and a radiation extracting efficiency or a light exit efficiency of a GaN system semiconductor light emitting device.

In order to accomplish the above mentioned object, the present invention provides a semiconductor light emitting device comprising a light emission layer, consisting of a GaN system semiconductor, which is interposed between an n type GaN system semiconductor layer and a p type GaN system semiconductor layer, wherein there is provided a Ga-doped $Mg_zZn_{1-z}O$ ($0 \leq z < 1$) electrode film.